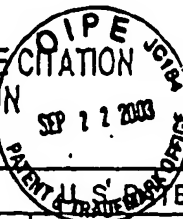


Form PTO-1449

INFORMATION DISCLOSURE
IN AN APPLICATION

(Use several sheets if necessary)



Document Number (Sequence)

TSMC-02-066

Application Number

10/600,393

Applicant

Chi-Chun Chen et al.

Filing Date

06/20/03

Group Art Unit

2822

PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	ALSO DATE IF APPROPRIATE
TMT	6110842	8/29/00	Okuno et al.	438	776	4/22/98
	6030862	2/29/00	Kepler	438	217	10/13/98
	5960289	9/28/99	Tsui et al.	438	275	6/22/98
	6262455	7/17/01	Lutze et al.	257	369	11/2/99
TMT	6037224	3/14/00	Buller et al.	438	258	5/2/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portinent Pages, Etc.)

EXAMINER

T. M. Thomas

DATE CONSIDERED

09-08-04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

2

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PATENT AND TRADEMARK OFFICE

Complete if Known

SHEET 1 OF 1

Application Number: 10/600,393

Filing Date: June 20, 2003

Applicant(s): Chi-Chun Chen et al.

Art Unit: 2822

Examiner Name: Thomas, Toniae M.

Attorney/Doctel Number: 2002-0066 / 24061.461

DEC 29 2004

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
XX	AA	6060289	09-28-1999	Isci et al. <i>Already considered</i>
XX	AB	6030062	02-20-2000	Kepler <i> </i>
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FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation

OTHER PRIOR ART		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume, issue number(s), publisher, city/country where published
<i>JMJ</i>	AH	G. LUCOVSKY et al., "Formation of thin film dielectrics by remove plasma-enhanced chemical-vapor deposition (remote PECVD)", Applied Surface Science, Volume 39, Issue 1-4, October 1989, Pages 33-36.
<i>JMJ</i>	AI	STANLEY WOLF et al., "Silicon Processing For The VLSI Era, Volume 1: Process Technology", Lattice Press, Sunset Beach, CA, 3 pages
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<i>JMJ</i>	AK	HOWARD CHIH-HAO WANG et al., "Arsenic/Phosphorus LDD Optimization by Taking Advantage of Phosphorus Transient Enhanced Diffusion for High Voltage Input/Output CMOS Devices", IEEE Transactions on Electron Devices, Volume 49, No. 1, January 2002, 5 pages.

T. M. Thomas 03/18/05